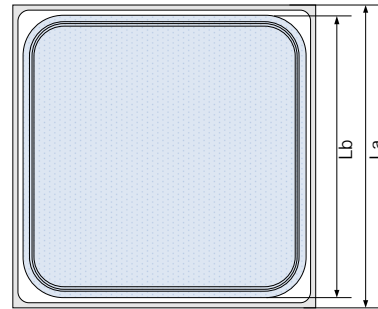


**2SB139100MA LOW IR SCHOTTKY BARRIER DIODE CHIPS**
**DESCRIPTION**

- ∅ 2SB139100MA is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- ∅ Due to special schottky barrier structure, the chips have very low reverse leakage current ( typical  $I_R=0.002mA@ V_r=100V$  ) and maximum 150°C operation junction temperature;
- ∅ Low power losses, high efficiency;
- ∅ Guard ring construction for transient protection;
- ∅ High ESD capability;
- ∅ High surge capability;
- ∅ Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- ∅ Chip Size: 1390 $\mu m$  X 1390 $\mu m$ ;
- ∅ Chip Thickness: 280 $\pm$ 20 $\mu m$ ;


**Chip Topography and Dimensions**
**La: Chip Size: 1.390mm;**
**Lb: Pad Size: 1.295mm;**
**ORDERING SPECIFICATIONS**

Product Name	Specification
2SB139100MAYY	For Axial leads package

**ABSOLUTE MAXIMUM RATINGS**

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	100	V
Average Forward Rectified Current	IFAV	3	A
Peak Forward Surge Current@8.3ms	IFSM	80	A
Maximum Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-40~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C)**

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=0.5mA	100	--	V
Forward Voltage	VF	IF=3A	--	0.85	V
Reverse Current	IR	VR=100V	--	0.5	mA